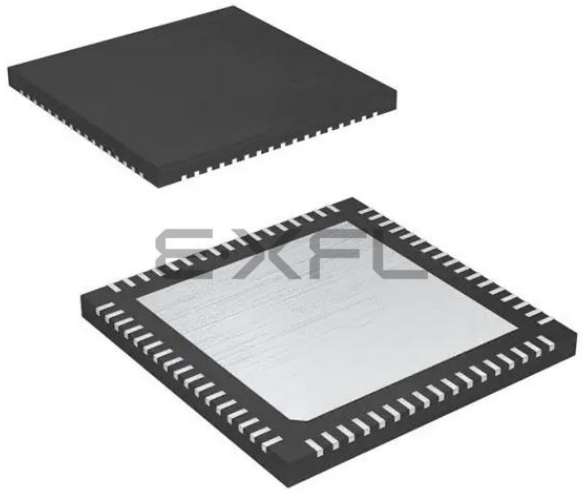

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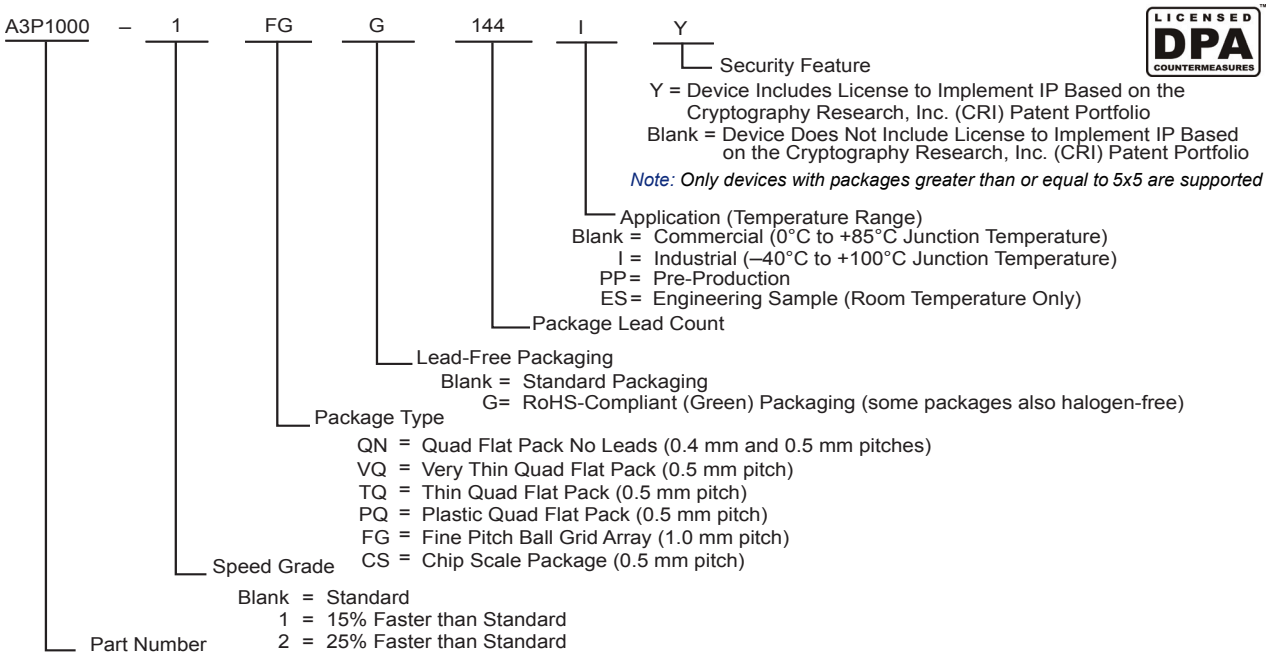
Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	49
Number of Gates	15000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	68-VFQFN Exposed Pad
Supplier Device Package	68-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a3p015-qng68

ProASIC3 Ordering Information



ProASIC3 Devices

A3P015 = 15,000 System Gates (A3P015 is not recommended for new designs.)
A3P030 = 30,000 System Gates
A3P060 = 60,000 System Gates
A3P125 = 125,000 System Gates
A3P250 = 250,000 System Gates
A3P400 = 400,000 System Gates
A3P600 = 600,000 System Gates
A3P1000 = 1,000,000 System Gates

ProASIC3 Devices with Cortex-M1

M1A3P250 = 250,000 System Gates
M1A3P400 = 400,000 System Gates
M1A3P600 = 600,000 System Gates
M1A3P1000 = 1,000,000 System Gates

ProASIC3 Device Status

ProASIC3 Devices	Status	Cortex-M1 Devices	Status
A3P015	Not recommended for new designs.		
A3P030	Production		
A3P060	Production		
A3P125	Production		
A3P250	Production	M1A3P250	Production
A3P400	Production	M1A3P400	Production
A3P600	Production	M1A3P600	Production
A3P1000	Production	M1A3P1000	Production

2 – ProASIC3 DC and Switching Characteristics

General Specifications

Operating Conditions

Stresses beyond those listed in Table 2-1 may cause permanent damage to the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Absolute Maximum Ratings are stress ratings only; functional operation of the device at these or any other conditions beyond those listed under the Recommended Operating Conditions specified in Table 2-2 on page 2-2 is not implied.

Table 2-1 • **Absolute Maximum Ratings**

Symbol	Parameter	Limits	Units
VCC	DC core supply voltage	–0.3 to 1.65	V
VJTAG	JTAG DC voltage	–0.3 to 3.75	V
VPUMP	Programming voltage	–0.3 to 3.75	V
VCCPLL	Analog power supply (PLL)	–0.3 to 1.65	V
VCCI	DC I/O output buffer supply voltage	–0.3 to 3.75	V
VMV	DC I/O input buffer supply voltage	–0.3 to 3.75	V
VI	I/O input voltage	–0.3 V to 3.6 V (when I/O hot insertion mode is enabled) –0.3 V to (VCCI + 1 V) or 3.6 V, whichever voltage is lower (when I/O hot-insertion mode is disabled)	V
T_{STG} [2]	Storage temperature	–65 to +150	°C
T_J [2]	Junction temperature	+125	°C

Notes:

1. *The device should be operated within the limits specified by the datasheet. During transitions, the input signal may undershoot or overshoot according to the limits shown in Table 2-4 on page 2-3.*
2. *VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information.*
3. *For flash programming and retention maximum limits, refer to Table 2-3 on page 2-3, and for recommended operating limits, refer to Table 2-2 on page 2-2.*

F_{CLK} is the global clock signal frequency.

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

P_{AC1}, P_{AC2}, P_{AC3}, and P_{AC4} are device-dependent.

Sequential Cells Contribution—$P_{S\text{-}CELL}$

$P_{S\text{-}CELL} = N_{S\text{-}CELL} * (P_{AC5} + \alpha_1 / 2 * P_{AC6}) * F_{CLK}$

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-16 on page 2-14.

F_{CLK} is the global clock signal frequency.

Combinatorial Cells Contribution—$P_{C\text{-}CELL}$

$P_{C\text{-}CELL} = N_{C\text{-}CELL} * \alpha_1 / 2 * P_{AC7} * F_{CLK}$

$N_{C\text{-}CELL}$ is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-16 on page 2-14.

F_{CLK} is the global clock signal frequency.

Routing Net Contribution—P_{NET}

$P_{NET} = (N_{S\text{-}CELL} + N_{C\text{-}CELL}) * \alpha_1 / 2 * P_{AC8} * F_{CLK}$

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

$N_{C\text{-}CELL}$ is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-16 on page 2-14.

F_{CLK} is the global clock signal frequency.

I/O Input Buffer Contribution—P_{INPUTS}

$P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * P_{AC9} * F_{CLK}$

N_{INPUTS} is the number of I/O input buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-16 on page 2-14.

F_{CLK} is the global clock signal frequency.

I/O Output Buffer Contribution—$P_{OUTPUTS}$

$P_{OUTPUTS} = N_{OUTPUTS} * \alpha_2 / 2 * \beta_1 * P_{AC10} * F_{CLK}$

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-16 on page 2-14.

β_1 is the I/O buffer enable rate—guidelines are provided in Table 2-17 on page 2-14.

F_{CLK} is the global clock signal frequency.

Timing Characteristics

Table 2-41 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	7.66	0.04	1.02	0.43	7.80	6.59	2.65	2.61	10.03	8.82	ns
	–1	0.56	6.51	0.04	0.86	0.36	6.63	5.60	2.25	2.22	8.54	7.51	ns
	–2	0.49	5.72	0.03	0.76	0.32	5.82	4.92	1.98	1.95	7.49	6.59	ns
4 mA	Std.	0.66	7.66	0.04	1.02	0.43	7.80	6.59	2.65	2.61	10.03	8.82	ns
	–1	0.56	6.51	0.04	0.86	0.36	6.63	5.60	2.25	2.22	8.54	7.51	ns
	–2	0.49	5.72	0.03	0.76	0.32	5.82	4.92	1.98	1.95	7.49	6.59	ns
6 mA	Std.	0.66	4.91	0.04	1.02	0.43	5.00	4.07	2.99	3.20	7.23	6.31	ns
	–1	0.56	4.17	0.04	0.86	0.36	4.25	3.46	2.54	2.73	6.15	5.36	ns
	–2	0.49	3.66	0.03	0.76	0.32	3.73	3.04	2.23	2.39	5.40	4.71	ns
8 mA	Std.	0.66	4.91	0.04	1.02	0.43	5.00	4.07	2.99	3.20	7.23	6.31	ns
	–1	0.56	4.17	0.04	0.86	0.36	4.25	3.46	2.54	2.73	6.15	5.36	ns
	–2	0.49	3.66	0.03	0.76	0.32	3.73	3.04	2.23	2.39	5.40	4.71	ns
12 mA	Std.	0.66	3.53	0.04	1.02	0.43	3.60	2.82	3.21	3.58	5.83	5.06	ns
	–1	0.56	3.00	0.04	0.86	0.36	3.06	2.40	2.73	3.05	4.96	4.30	ns
	–2	0.49	2.64	0.03	0.76	0.32	2.69	2.11	2.40	2.68	4.36	3.78	ns
16 mA	Std.	0.66	3.33	0.04	1.02	0.43	3.39	2.56	3.26	3.68	5.63	4.80	ns
	–1	0.56	2.83	0.04	0.86	0.36	2.89	2.18	2.77	3.13	4.79	4.08	ns
	–2	0.49	2.49	0.03	0.76	0.32	2.53	1.91	2.44	2.75	4.20	3.58	ns
24 mA	Std.	0.66	3.08	0.04	1.02	0.43	3.13	2.12	3.32	4.06	5.37	4.35	ns
	–1	0.56	2.62	0.04	0.86	0.36	2.66	1.80	2.83	3.45	4.57	3.70	ns
	–2	0.49	2.30	0.03	0.76	0.32	2.34	1.58	2.48	3.03	4.01	3.25	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-42 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	10.26	0.04	1.02	0.43	10.45	8.90	2.64	2.46	12.68	11.13	ns
	–1	0.56	8.72	0.04	0.86	0.36	8.89	7.57	2.25	2.09	10.79	9.47	ns
	–2	0.49	7.66	0.03	0.76	0.32	7.80	6.64	1.98	1.83	9.47	8.31	ns
4 mA	Std.	0.66	10.26	0.04	1.02	0.43	10.45	8.90	2.64	2.46	12.68	11.13	ns
	–1	0.56	8.72	0.04	0.86	0.36	8.89	7.57	2.25	2.09	10.79	9.47	ns
	–2	0.49	7.66	0.03	0.76	0.32	7.80	6.64	1.98	1.83	9.47	8.31	ns
6 mA	Std.	0.66	7.27	0.04	1.02	0.43	7.41	6.28	2.98	3.04	9.65	8.52	ns
	–1	0.56	6.19	0.04	0.86	0.36	6.30	5.35	2.54	2.59	8.20	7.25	ns
	–2	0.49	5.43	0.03	0.76	0.32	5.53	4.69	2.23	2.27	7.20	6.36	ns
8 mA	Std.	0.66	7.27	0.04	1.02	0.43	7.41	6.28	2.98	3.04	9.65	8.52	ns
	–1	0.56	6.19	0.04	0.86	0.36	6.30	5.35	2.54	2.59	8.20	7.25	ns
	–2	0.49	5.43	0.03	0.76	0.32	5.53	4.69	2.23	2.27	7.20	6.36	ns
12 mA	Std.	0.66	5.58	0.04	1.02	0.43	5.68	4.87	3.21	3.42	7.92	7.11	ns
	–1	0.56	4.75	0.04	0.86	0.36	4.84	4.14	2.73	2.91	6.74	6.05	ns
	–2	0.49	4.17	0.03	0.76	0.32	4.24	3.64	2.39	2.55	5.91	5.31	ns
16 mA	Std.	0.66	5.21	0.04	1.02	0.43	5.30	4.56	3.26	3.51	7.54	6.80	ns
	–1	0.56	4.43	0.04	0.86	0.36	4.51	3.88	2.77	2.99	6.41	5.79	ns
	–2	0.49	3.89	0.03	0.76	0.32	3.96	3.41	2.43	2.62	5.63	5.08	ns
24 mA	Std.	0.66	4.85	0.04	1.02	0.43	4.94	4.54	3.32	3.88	7.18	6.78	ns
	–1	0.56	4.13	0.04	0.86	0.36	4.20	3.87	2.82	3.30	6.10	5.77	ns
	–2	0.49	3.62	0.03	0.76	0.32	3.69	3.39	2.48	2.90	5.36	5.06	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Timing Characteristics

Table 2-50 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	4 mA	Std.	0.60	11.84	0.04	1.02	0.43	11.84	10.00	4.10	4.04	15.23	13.40	ns
		–1	0.51	10.07	0.04	0.86	0.36	10.07	8.51	3.48	3.44	12.96	11.40	ns
		–2	0.45	8.84	0.03	0.76	0.32	8.84	7.47	3.06	3.02	11.38	10.00	ns
100 µA	6 mA	Std.	0.60	7.59	0.04	1.02	0.43	7.59	6.18	4.62	4.95	10.98	9.57	ns
		–1	0.51	6.45	0.04	0.86	0.36	6.45	5.25	3.93	4.21	9.34	8.14	ns
		–2	0.45	5.67	0.03	0.76	0.32	5.67	4.61	3.45	3.70	8.20	7.15	ns
100 µA	8 mA	Std.	0.60	7.59	0.04	1.02	0.43	7.59	6.18	4.62	4.95	10.98	9.57	ns
		–1	0.51	6.45	0.04	0.86	0.36	6.45	5.25	3.93	4.21	9.34	8.14	ns
		–2	0.45	5.67	0.03	0.76	0.32	5.67	4.61	3.45	3.70	8.20	7.15	ns
100 µA	12 mA	Std.	0.60	5.46	0.04	1.02	0.43	5.46	4.29	4.97	5.54	8.86	7.68	ns
		–1	0.51	4.65	0.04	0.86	0.36	4.65	3.65	4.22	4.71	7.53	6.54	ns
		–2	0.45	4.08	0.03	0.76	0.32	4.08	3.20	3.71	4.14	6.61	5.74	ns
100 µA	16 mA	Std.	0.60	5.15	0.04	1.02	0.43	5.15	3.89	5.04	5.69	8.55	7.29	ns
		–1	0.51	4.38	0.04	0.86	0.36	4.38	3.31	4.29	4.84	7.27	6.20	ns
		–2	0.45	3.85	0.03	0.76	0.32	3.85	2.91	3.77	4.25	6.38	5.44	ns
100 µA	24 mA	Std.	0.60	4.75	0.04	1.02	0.43	4.75	3.22	5.14	6.28	8.15	6.61	ns
		–1	0.51	4.04	0.04	0.86	0.36	4.04	2.74	4.37	5.34	6.93	5.62	ns
		–2	0.45	3.55	0.03	0.76	0.32	3.55	2.40	3.84	4.69	6.09	4.94	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *Software default selection highlighted in gray.*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-51 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	2 mA	Std.	0.60	15.86	0.04	1.54	0.43	15.86	13.51	4.09	3.80	19.25	16.90	ns
		–1	0.51	13.49	0.04	1.31	0.36	13.49	11.49	3.48	3.23	16.38	14.38	ns
		–2	0.45	11.84	0.03	1.15	0.32	11.84	10.09	3.05	2.84	14.38	12.62	ns
100 µA	4 mA	Std.	0.60	11.25	0.04	1.54	0.43	11.25	9.54	4.61	4.70	14.64	12.93	ns
		–1	0.51	9.57	0.04	1.31	0.36	9.57	8.11	3.92	4.00	12.46	11.00	ns
		–2	0.45	8.40	0.03	1.15	0.32	8.40	7.12	3.44	3.51	10.93	9.66	ns
100 µA	6 mA	Std.	0.60	11.25	0.04	1.54	0.43	11.25	9.54	4.61	4.70	14.64	12.93	ns
		–1	0.51	9.57	0.04	1.31	0.36	9.57	8.11	3.92	4.00	12.46	11.00	ns
		–2	0.45	8.40	0.03	1.15	0.32	8.40	7.12	3.44	3.51	10.93	9.66	ns
100 µA	8 mA	Std.	0.60	8.63	0.04	1.54	0.43	8.63	7.39	4.96	5.28	12.02	10.79	ns
		–1	0.51	7.34	0.04	1.31	0.36	7.34	6.29	4.22	4.49	10.23	9.18	ns
		–2	0.45	6.44	0.03	1.15	0.32	6.44	5.52	3.70	3.94	8.98	8.06	ns
100 µA	16 mA	Std.	0.60	8.05	0.04	1.54	0.43	8.05	6.93	5.03	5.43	11.44	10.32	ns
		–1	0.51	6.85	0.04	1.31	0.36	6.85	5.90	4.28	4.62	9.74	8.78	ns
		–2	0.45	6.01	0.03	1.15	0.32	6.01	5.18	3.76	4.06	8.55	7.71	ns
100 µA	24 mA	Std.	0.60	7.50	0.04	1.54	0.43	7.50	6.90	5.13	6.00	10.89	10.29	ns
		–1	0.51	6.38	0.04	1.31	0.36	6.38	5.87	4.36	5.11	9.27	8.76	ns
		–2	0.45	5.60	0.03	1.15	0.32	5.60	5.15	3.83	4.48	8.13	7.69	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

1.8 V LVCMOS

Low-voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

Table 2-66 • Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA[3]	Max mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	2	2	11	9	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	4	4	22	17	10	10
6 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	6	6	44	35	10	10
8 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	8	8	51	45	10	10
12 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	12	12	74	91	10	10
16 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	16	16	74	91	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-67 • Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA[3]	Max mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	2	2	11	9	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4	22	17	10	10
6 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	6	6	44	35	10	10
8 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	8	8	44	35	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN <V CCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-77 • Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O Banks

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	2	2	16	13	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	4	4	33	25	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-78 • Minimum and Maximum DC Input and Output Levels Applicable to Standard I/O Banks

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

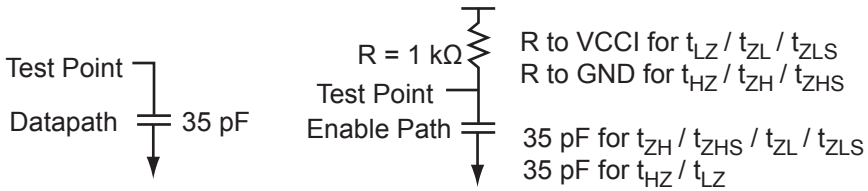


Figure 2-10 • AC Loading

Table 2-79 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	1.5	0.75	35

*Note: *Measuring point = V_{trip}. See Table 2-22 on page 2-22 for a complete table of trip points.*

Table 2-117 • RAM512X18
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

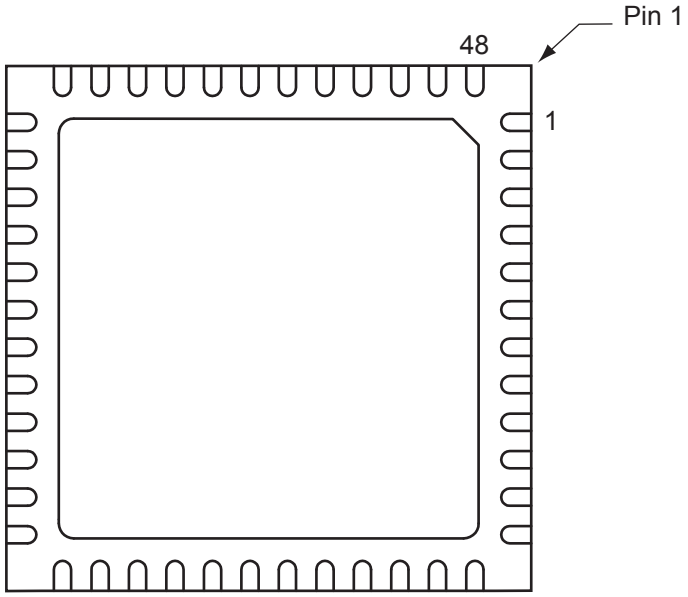
Parameter	Description	–2	–1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.13	0.15	0.17	ns
t_{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t_{DS}	Input data (WD) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (WD) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	2.16	2.46	2.89	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	0.90	1.02	1.20	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.50	0.43	0.38	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.59	0.50	0.44	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to data out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. *For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

4 – Package Pin Assignments

QN48 – Bottom View



Note: The die attach paddle center of the package is tied to ground (GND).

Note

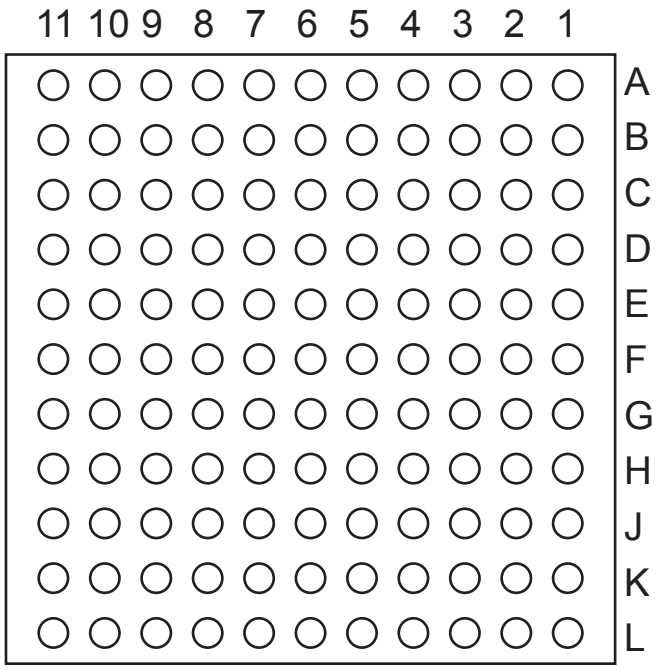
For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

QN48	
Pin Number	**A3P030 Function**
1	IO82RSB1
2	GEC0/IO73RSB1
3	GEA0/IO72RSB1
4	GEB0/IO71RSB1
5	GND
6	VCCIB1
7	IO68RSB1
8	IO67RSB1
9	IO66RSB1
10	IO65RSB1
11	IO64RSB1
12	IO62RSB1
13	IO61RSB1
14	IO60RSB1
15	IO57RSB1
16	IO55RSB1
17	IO53RSB1
18	VCC
19	VCCIB1
20	IO46RSB1
21	IO42RSB1
22	TCK
23	TDI
24	TMS
25	VPUMP
26	TDO
27	TRST
28	VJTAG
29	IO38RSB0
30	GDB0/IO34RSB0
31	GDA0/IO33RSB0
32	GDC0/IO32RSB0
33	VCCIB0
34	GND
35	VCC
36	IO25RSB0

QN48	
Pin Number	**A3P030 Function**
37	IO24RSB0
38	IO22RSB0
39	IO20RSB0
40	IO18RSB0
41	IO16RSB0
42	IO14RSB0
43	IO10RSB0
44	IO08RSB0
45	IO06RSB0
46	IO04RSB0
47	IO02RSB0
48	IO00RSB0

QN132	
Pin Number	**A3P250 Function**
C17	IO74RSB2
C18	VCCIB2
C19	TCK
C20	VMV2
C21	VPUMP
C22	VJTAG
C23	VCCIB1
C24	IO53NSB1
C25	IO51NPB1
C26	GCA1/IO50PPB1
C27	GCC0/IO48NDB1
C28	VCCIB1
C29	IO42NDB1
C30	GNDQ
C31	GBA1/IO40RSB0
C32	GBB0/IO37RSB0
C33	VCC
C34	IO24RSB0
C35	IO19RSB0
C36	IO16RSB0
C37	IO10RSB0
C38	VCCIB0
C39	GAB1/IO03RSB0
C40	VMV0
D1	GND
D2	GND
D3	GND
D4	GND

CS121 – Bottom View



Note: The die attach paddle center of the package is tied to ground (GND).

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

PQ208	
Pin Number	A3P400 Function
1	GND
2	GAA2/IO155UDB3
3	IO155VDB3
4	GAB2/IO154UDB3
5	IO154VDB3
6	GAC2/IO153UDB3
7	IO153VDB3
8	IO152UDB3
9	IO152VDB3
10	IO151UDB3
11	IO151VDB3
12	IO150PDB3
13	IO150NDB3
14	IO149PDB3
15	IO149NDB3
16	VCC
17	GND
18	VCCIB3
19	IO148PDB3
20	IO148NDB3
21	GFC1/IO147PDB3
22	GFC0/IO147NDB3
23	GFB1/IO146PDB3
24	GFB0/IO146NDB3
25	VCOMPLF
26	GFA0/IO145NPB3
27	VCCPLF
28	GFA1/IO145PPB3
29	GND
30	GFA2/IO144PDB3
31	IO144NDB3
32	GFB2/IO143PDB3
33	IO143NDB3
34	GFC2/IO142PDB3
35	IO142NDB3
36	NC

PQ208	
Pin Number	A3P400 Function
37	IO141PSB3
38	IO140PDB3
39	IO140NDB3
40	VCCIB3
41	GND
42	IO138PDB3
43	IO138NDB3
44	GEC1/IO137PDB3
45	GEC0/IO137NDB3
46	GEB1/IO136PDB3
47	GEB0/IO136NDB3
48	GEA1/IO135PDB3
49	GEA0/IO135NDB3
50	VMV3
51	GNDQ
52	GND
53	VMV2
54	NC
55	GEA2/IO134RSB2
56	GEB2/IO133RSB2
57	GEC2/IO132RSB2
58	IO131RSB2
59	IO130RSB2
60	IO129RSB2
61	IO128RSB2
62	VCCIB2
63	IO125RSB2
64	IO123RSB2
65	GND
66	IO121RSB2
67	IO119RSB2
68	IO117RSB2
69	IO115RSB2
70	IO113RSB2
71	VCC
72	VCCIB2

PQ208	
Pin Number	A3P400 Function
73	IO112RSB2
74	IO111RSB2
75	IO110RSB2
76	IO109RSB2
77	IO108RSB2
78	IO107RSB2
79	IO106RSB2
80	IO104RSB2
81	GND
82	IO102RSB2
83	IO101RSB2
84	IO100RSB2
85	IO99RSB2
86	IO98RSB2
87	IO97RSB2
88	VCC
89	VCCIB2
90	IO94RSB2
91	IO92RSB2
92	IO90RSB2
93	IO88RSB2
94	IO86RSB2
95	IO84RSB2
96	GDC2/IO82RSB2
97	GND
98	GDB2/IO81RSB2
99	GDA2/IO80RSB2
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV2
105	GND
106	VPUMP
107	NC
108	TDO

PQ208	
Pin Number	A3P1000 Function
1	GND
2	GAA2/IO225PDB3
3	IO225NDB3
4	GAB2/IO224PDB3
5	IO224NDB3
6	GAC2/IO223PDB3
7	IO223NDB3
8	IO222PDB3
9	IO222NDB3
10	IO220PDB3
11	IO220NDB3
12	IO218PDB3
13	IO218NDB3
14	IO216PDB3
15	IO216NDB3
16	VCC
17	GND
18	VCCIB3
19	IO212PDB3
20	IO212NDB3
21	GFC1/IO209PDB3
22	GFC0/IO209NDB3
23	GFB1/IO208PDB3
24	GFB0/IO208NDB3
25	VCOMPLF
26	GFA0/IO207NPB3
27	VCCPLF
28	GFA1/IO207PPB3
29	GND
30	GFA2/IO206PDB3
31	IO206NDB3
32	GFB2/IO205PDB3
33	IO205NDB3
34	GFC2/IO204PDB3
35	IO204NDB3
36	VCC

PQ208	
Pin Number	A3P1000 Function
37	IO199PDB3
38	IO199NDB3
39	IO197PSB3
40	VCCIB3
41	GND
42	IO191PDB3
43	IO191NDB3
44	GEC1/IO190PDB3
45	GEC0/IO190NDB3
46	GEB1/IO189PDB3
47	GEB0/IO189NDB3
48	GEA1/IO188PDB3
49	GEA0/IO188NDB3
50	VMV3
51	GNDQ
52	GND
53	VMV2
54	GEA2/IO187RSB2
55	GEB2/IO186RSB2
56	GEC2/IO185RSB2
57	IO184RSB2
58	IO183RSB2
59	IO182RSB2
60	IO181RSB2
61	IO180RSB2
62	VCCIB2
63	IO178RSB2
64	IO176RSB2
65	GND
66	IO174RSB2
67	IO172RSB2
68	IO170RSB2
69	IO168RSB2
70	IO166RSB2
71	VCC
72	VCCIB2

PQ208	
Pin Number	A3P1000 Function
73	IO162RSB2
74	IO160RSB2
75	IO158RSB2
76	IO156RSB2
77	IO154RSB2
78	IO152RSB2
79	IO150RSB2
80	IO148RSB2
81	GND
82	IO143RSB2
83	IO141RSB2
84	IO139RSB2
85	IO137RSB2
86	IO135RSB2
87	IO133RSB2
88	VCC
89	VCCIB2
90	IO128RSB2
91	IO126RSB2
92	IO124RSB2
93	IO122RSB2
94	IO120RSB2
95	IO118RSB2
96	GDC2/IO116RSB2
97	GND
98	GDB2/IO115RSB2
99	GDA2/IO114RSB2
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV2
105	GND
106	VPUMP
107	GNDQ
108	TDO

FG256	
Pin Number	**A3P600 Function**
P9	IO107RSB2
P10	IO104RSB2
P11	IO97RSB2
P12	VMV1
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO88NDB1
R1	GEA1/IO144PDB3
R2	GEA0/IO144NDB3
R3	IO139RSB2
R4	GEC2/IO141RSB2
R5	IO132RSB2
R6	IO127RSB2
R7	IO121RSB2
R8	IO114RSB2
R9	IO109RSB2
R10	IO105RSB2
R11	IO98RSB2
R12	IO96RSB2
R13	GDB2/IO90RSB2
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO137RSB2
T3	GEB2/IO142RSB2
T4	IO134RSB2
T5	IO125RSB2
T6	IO123RSB2
T7	IO118RSB2
T8	IO115RSB2
T9	IO111RSB2
T10	IO106RSB2
T11	IO102RSB2
T12	GDC2/IO91RSB2

FG256	
Pin Number	**A3P600 Function**
T13	IO93RSB2
T14	GDA2/IO89RSB2
T15	TMS
T16	GND

FG484	
Pin Number	A3P600 Function
E21	NC
E22	NC
F1	NC
F2	NC
F3	NC
F4	IO173NDB3
F5	IO174NDB3
F6	VMV3
F7	IO07RSB0
F8	GAC0/IO04RSB0
F9	GAC1/IO05RSB0
F10	IO20RSB0
F11	IO24RSB0
F12	IO33RSB0
F13	IO39RSB0
F14	IO44RSB0
F15	GBC0/IO54RSB0
F16	IO51RSB0
F17	VMV0
F18	IO61NPB1
F19	IO63PDB1
F20	NC
F21	NC
F22	NC
G1	IO170NDB3
G2	IO170PDB3
G3	NC
G4	IO171NDB3
G5	IO171PDB3
G6	GAC2/IO172PDB3
G7	IO06RSB0
G8	GNDQ
G9	IO10RSB0
G10	IO19RSB0
G11	IO26RSB0
G12	IO30RSB0

FG484	
Pin Number	A3P600 Function
G13	IO40RSB0
G14	IO45RSB0
G15	GNDQ
G16	IO50RSB0
G17	GBB2/IO61PPB1
G18	IO53RSB0
G19	IO63NDB1
G20	NC
G21	NC
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO166PDB3
H5	IO167NPB3
H6	IO172NDB3
H7	IO169NDB3
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO25RSB0
H12	IO31RSB0
H13	VCCIB0
H14	VCCIB0
H15	VMV1
H16	GBC2/IO62PDB1
H17	IO67PPB1
H18	IO64PPB1
H19	IO66PDB1
H20	VCC
H21	NC
H22	NC
J1	NC
J2	NC
J3	NC
J4	IO166NDB3

FG484	
Pin Number	A3P600 Function
J5	IO168NPB3
J6	IO167PPB3
J7	IO169PDB3
J8	VCCIB3
J9	GND
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	GND
J15	VCCIB1
J16	IO62NDB1
J17	IO64NPB1
J18	IO65PPB1
J19	IO66NDB1
J20	NC
J21	IO68PDB1
J22	IO68NDB1
K1	IO157PDB3
K2	IO157NDB3
K3	NC
K4	IO165NDB3
K5	IO165PDB3
K6	IO168PPB3
K7	GFC1/IO164PPB3
K8	VCCIB3
K9	VCC
K10	GND
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB1
K16	GCC1/IO69PPB1
K17	IO65NPB1
K18	IO75PDB1

Revision	Changes	Page
Revision 9 (Oct 2009) Product Brief v1.3	The CS121 package was added to table under "Features and Benefits" section, the "I/Os Per Package 1" table, Table 1 • ProASIC3 FPGAs Package Sizes Dimensions, "ProASIC3 Ordering Information", and the "Temperature Grade Offerings" table.	I – IV
	"ProASIC3 Ordering Information" was revised to include the fact that some RoHS compliant packages are halogen-free.	IV
Packaging v1.5	The "CS121 – Bottom View" figure and pin table for A3P060 are new.	4-15
Revision 8 (Aug 2009) Product Brief v1.2	All references to M7 devices (CoreMP7) and speed grade –F were removed from this document.	N/A
	Table 1-1 I/O Standards supported is new.	1-7
	The I/Os with Advanced I/O Standards section was revised to add definitions of hot-swap and cold-sparing.	1-7
DC and Switching Characteristics v1.4	3.3 V LVCMOS and 1.2 V LVCMOS Wide Range support was added to the datasheet. This affects all tables that contained 3.3 V LVCMOS and 1.2 V LVCMOS data.	N/A
	I_{IL} and I_{IH} input leakage current information was added to all "Minimum and Maximum DC Input and Output Levels" tables.	N/A
	–F was removed from the datasheet. The speed grade is no longer supported.	N/A
	The notes in Table 2-2 • Recommended Operating Conditions 1 were updated.	2-2
	Table 2-4 • Overshoot and Undershoot Limits 1 was updated.	2-3
	Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays was updated.	2-6
	In Table 2-116 • RAM4K9, the following specifications were removed: t_{WRO} t_{CCKH}	2-96
	In Table 2-117 • RAM512X18, the following specifications were removed: t_{WRO} t_{CCKH}	2-97
	In the title of Table 2-74 • 1.8 V LVCMOS High Slew, VCCI had a typo. It was changed from 3.0 V to 1.7 V.	2-58
Revision 7 (Feb 2009) Product Brief v1.1	The "Advanced I/O" section was revised to add a bullet regarding wide range power supply voltage support.	I
	The table under "Features and Benefits" section, was updated to include a value for typical equivalent macrocells for A3P250.	I
	The QN48 package was added to the following tables: the table under "Features and Benefits" section, "I/Os Per Package 1" "ProASIC3 FPGAs Package Sizes Dimensions", and "Temperature Grade Offerings". The number of singled-ended I/Os for QN68 was added to the "I/Os Per Package 1" table.	N/A
	The Wide Range I/O Support section is new.	1-7
Revision 6 (Dec 2008) Packaging v1.4	The "QN48 – Bottom View" section is new.	4-1
	The "QN68" pin table for A3P030 is new.	4-5

Revision	Changes	Page
v2.0 (continued)	Table 3-20 • Summary of I/O Timing Characteristics—Software Default Settings (Advanced) and Table 3-21 • Summary of I/O Timing Characteristics—Software Default Settings (Standard Plus) were updated.	3-20 to 3-20
	Table 3-11 • Different Components Contributing to Dynamic Power Consumption in ProASIC3 Devices was updated.	3-9
	Table 3-24 • I/O Output Buffer Maximum Resistances1 (Advanced) and Table 3-25 • I/O Output Buffer Maximum Resistances1 (Standard Plus) were updated.	3-22 to 3-22
	Table 3-17 • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial and Industrial Conditions was updated.	3-18
	Table 3-28 • I/O Short Currents IOSH/IOSL (Advanced) and Table 3-29 • I/O Short Currents IOSH/IOSL (Standard Plus) were updated.	3-24 to 3-26
	The note in Table 3-32 • I/O Input Rise Time, Fall Time, and Related I/O Reliability was updated.	3-27
	Figure 3-33 • Write Access After Write onto Same Address, Figure 3-34 • Read Access After Write onto Same Address, and Figure 3-35 • Write Access After Read onto Same Address are new.	3-82 to 3-84
	Figure 3-43 • Timing Diagram was updated.	3-96
	Ambient was deleted from the "Speed Grade and Temperature Grade Matrix".	iv
	Notes were added to the package diagrams identifying if they were top or bottom view.	N/A
	The A3P030 "132-Pin QFN" table is new.	4-2
	The A3P060 "132-Pin QFN" table is new.	4-4
	The A3P125 "132-Pin QFN" table is new.	4-6
	The A3P250 "132-Pin QFN" table is new.	4-8
	The A3P030 "100-Pin VQFP" table is new.	4-11
Advance v0.7 (January 2007)	In the "I/Os Per Package" table, the I/O numbers were added for A3P060, A3P125, and A3P250. The A3P030-VQ100 I/O was changed from 79 to 77.	ii
Advance v0.6 (April 2006)	The term flow-through was changed to pass-through.	N/A
	Table 1 was updated to include the QN132.	ii
	The "I/Os Per Package" table was updated with the QN132. The footnotes were also updated. The A3P400-FG144 I/O count was updated.	ii
	"Automotive ProASIC3 Ordering Information" was updated with the QN132.	iii
	"Temperature Grade Offerings" was updated with the QN132.	iii
	B-LVDS and M-LDVS are new I/O standards added to the datasheet.	N/A
	The term flow-through was changed to pass-through.	N/A
	Figure 2-7 • Efficient Long-Line Resources was updated.	2-7
	The footnotes in Figure 2-15 • Clock Input Sources Including CLKBUF, CLKBUF_LVDS/LVPECL, and CLKINT were updated.	2-16
	The Delay Increments in the Programmable Delay Blocks specification in Figure 2-24 • ProASIC3E CCC Options.	2-24
	The "SRAM and FIFO" section was updated.	2-21